



PZT5401

PNP EPITAXIAL SILICON TRANSISTOR

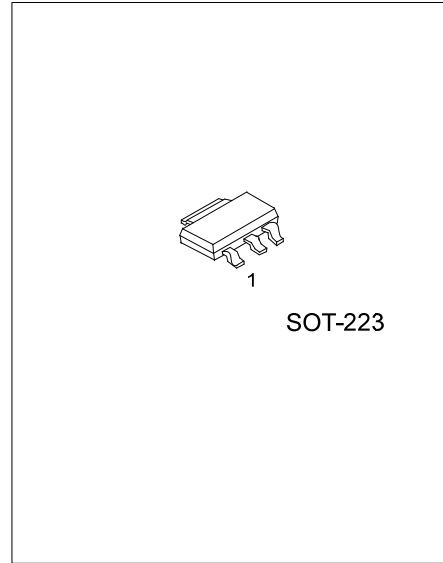
HIGH VOLTAGE SWITCHING TRANSISTOR

■ FEATURES

- * High Collector-Emitter Voltage: $V_{CE0}=-150V$
- * High current gain

■ APPLICATIONS

- * Telephone Switching Circuit
- * Amplifier



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen-Free		1	2	3	
PZT5401L-x-AA3-R	PZT5401G-x-AA3-R	SOT-223	B	C	E	Tape Reel

Note: Pin Assignment: B: Base C: Collector E: Emitter

<p>PZT5401L-x-AE3-R</p>	<ul style="list-style-type: none"> (1) R: Tape Reel (2) AE3: SOT-23 (3) x: refer to Classification of h_{FE} (4) G: Halogen Free, L: Lead Free Plating
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■ ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CB0}	-160	V
Collector-Emitter Voltage	V_{CE0}	-150	V
Emitter-Base Voltage	V_{EB0}	-5	V
DC Collector Current	I_C	-600	mA
Power Dissipation	P_D	2	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-40 ~ +150	$^\circ\text{C}$

■ ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	V_{CB0}	$I_C = 100\mu\text{A}, I_E = 0$	-160			V
Collector-Emitter Breakdown Voltage	V_{CE0}	$I_C = 1\text{mA}, I_B = 0$	-150			V
Emitter-Base Breakdown Voltage	V_{EB0}	$I_E = 10\mu\text{A}, I_C = 0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 120\text{V}, I_E = 0$			-50	nA
Emitter Cut-off Current	I_{EBO}	$V_{BE} = -3\text{V}, I_C = 0$			-50	nA
DC Current Gain(note)	h_{FE}	$V_{CE} = -5\text{V}, I_C = -1\text{mA}$	80		400	
		$V_{CE} = -5\text{V}, I_C = -10\text{mA}$	80			
		$V_{CE} = -5\text{V}, I_C = -50\text{mA}$	80			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$			-0.2 -0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$			-1 -1	V
Current Gain Bandwidth Product	f_T	$V_{CE} = -10\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$	100		400	MHz
Output Capacitance	C_{OB}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			6.0	pF
Noise Figure	N_F	$I_C = -0.25\text{mA}, V_{CE} = -5\text{V}$ $R_S = 1\text{k}\Omega, f = 10\text{Hz} \sim 15.7\text{kHz}$			8	dB

Note: Pulse test: $P_W < 300\mu\text{s}$, Duty Cycle $< 2\%$

■ CLASSIFICATION OF h_{FE}

RANK	A	B	C
RANGE	80-170	150-240	200-400

■ TYPICAL CHARACTERISTICS

Fig.1 Collector output Capacitance

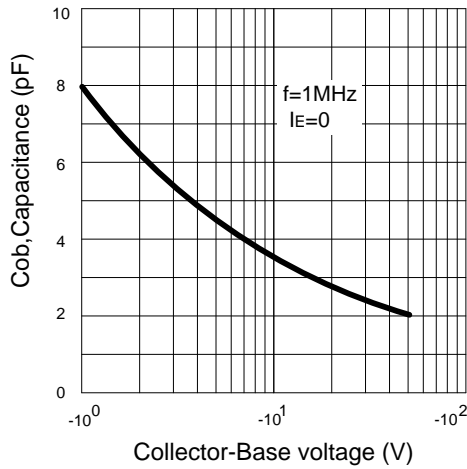


Fig.2 DC current Gain

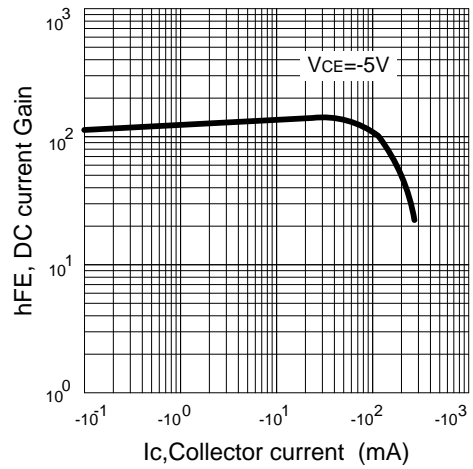


Fig.3 Base-Emitter on Voltage

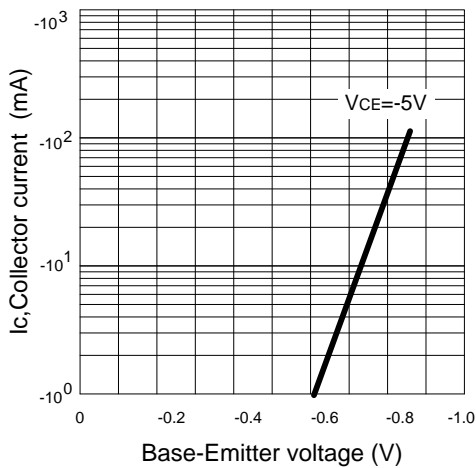


Fig.4 Saturation voltage

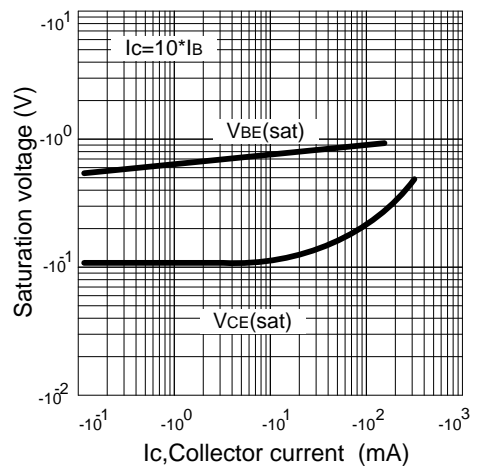
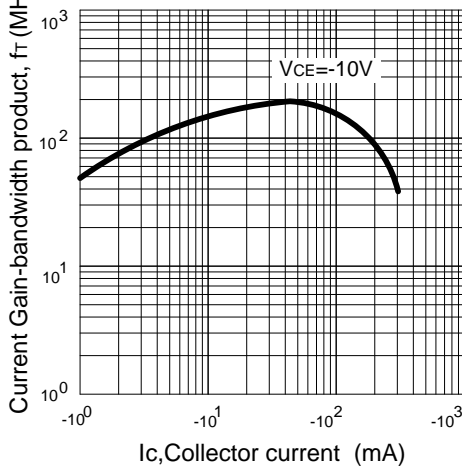


Fig.5 Current gain-bandwidth product



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